imall

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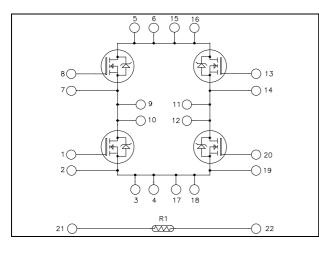
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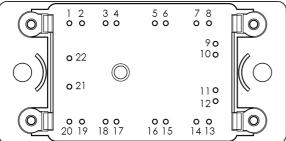
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Full bridge Super Junction MOSFET Power Module





Pins 5/6/15/16 ; 3/4/17/18 ; 9/10 ; 11/12 must be shorted together

APTC60HM83FT2G

$\begin{vmatrix} V_{DSS} = 600V \\ R_{DSon} = 83m\Omega \max @ Tj = 25^{\circ}C \\ I_{D} = 36A @ Tc = 25^{\circ}C \end{vmatrix}$

Application

- Welding converters
- Switched Mode Power Supplies
- Uninterruptible Power Supplies
- Motor control

Features

CoolMOSTM

- Ultra low R_{DSon}
- Low Miller capacitance
- Ultra low gate charge
- Avalanche energy rated
- Fast intrinsic diode
- Very rugged
- Very low stray inductance
- Internal thermistor for temperature monitoring
- High level of integration

Benefits

- Outstanding performance at high frequency operation
- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- Solderable terminals both for power and signal for easy PCB mounting
- Low profile
- RoHS Compliant

All ratings (a) $T_j = 25^{\circ}C$ unless otherwise specified

Absolute maximum ratings (per CoolMOSTM)

Symbol	Parameter		Max ratings	Unit	
V _{DSS}	Drain - Source Breakdown Voltage		600	V	
I _D	Continuous Drain Current	$T_c = 25^{\circ}C$ $T_c = 80^{\circ}C$	<u>36</u> 27	А	
I _{DM}	Pulsed Drain current	$1_{c} - 80 C$	100	A	
V _{GS}	Gate - Source Voltage		±20	V	
R _{DSon}	Drain - Source ON Resistance		83	mΩ	
P _D	Maximum Power Dissipation $T_c = 25^{\circ}C$		250	W	
I _{AR}	Avalanche current (repetitive and non repetitive)		20	Α	
E _{AR}	Repetitive Avalanche Energy		1	mJ	
E _{AS}	Single Pulse Avalanche Energy		1800	IIIJ	

CAUTION: These Devices are sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed. See application note APT0502 on www.microsemi.com



Electrical Characteristics (per CoolMOSTM)

Symbol	Characteristic	Test Conditions	Min	Тур	Max	Unit
I _{DSS}	Zero Gate Voltage Drain Current	$V_{GS} = 0V, V_{DS} = 600V$ $T_j = 25^{\circ}C$			50	μA
		$V_{GS} = 0V, V_{DS} = 600V$ $T_j = 125^{\circ}C$			5	mA
R _{DS(on)}	Drain – Source on Resistance	$V_{GS} = 10V, I_D = 18A$			83	mΩ
V _{GS(th)}	Gate Threshold Voltage	$V_{GS} = V_{DS}, I_D = 3mA$	3	4	5	V
I _{GSS}	Gate – Source Leakage Current	$V_{GS} = \pm 20 V, V_{DS} = 0V$			±100	nA

Dynamic Characteristics (per CoolMOSTM)

Symbol	<i>Characteristic</i>	Test Conditions		Min	Тур	Max	Unit
C _{iss}	Input Capacitance	$V_{GS} = 0V$			7290		
C _{oss}	Output Capacitance	$V_{\rm DS} = 25 V$	$V_{DS} = 25V$ f = 1MHz		1735		pF
C _{rss}	Reverse Transfer Capacitance	f = 1 MHz			41		
Q_{g}	Total gate Charge	$V_{GS} = 10V$	$V_{CS} = 10V$		255		
Q_{gs}	Gate – Source Charge	$V_{Bus} = 300V$			43		nC
Q_{gd}	Gate – Drain Charge	$I_D = 36A$			135		
T _{d(on)}	Turn-on Delay Time	Inductive Switching @ 125°C			21		
T_{r}	Rise Time		$V_{GS} = 15V$		30		
T _{d(off)}	Turn-off Delay Time	$I_{\rm D} = 36A$	$V_{Bus} = 400V$ $I_{D} = 36A$		240		ns
$T_{\rm f}$	Fall Time	$R_G = 5\Omega$			52		
E_{off}	Turn-off Switching Energy	Inductive switching $V_{GS} = 15V$, $I_D = 36A$ $R_G = 5\Omega$, $V_{Bus} = 400V$	T _J =25°C		590		1
$\mathrm{E}_{\mathrm{off}}$	Turn-off Switching Energy		T _J =125°C		725		μJ
R_{thJC}	Junction to Case Thermal Resistant	ce				0.5	°C/W

Source - Drain diode ratings and characteristics (per CoolMOSTM)

Symbol	Characteristic	Test Conditions		Min	Тур	Max	Unit
Is	Continuous Source current		$Tc = 25^{\circ}C$		36		А
	(Body diode)		$Tc = 80^{\circ}C$		27		A
V _{SD}	Diode Forward Voltage	$V_{GS} = 0V, I_S = -36A$				1.2	V
dv/dt	Peak Diode Recovery					40	V/ns
t _{rr}	Reverse Recovery Time	$I_{\rm S} = -36A$ $V_{\rm R} = 400V$	$T_j = 125^{\circ}C$		350		ns
Qrr	Reverse Recovery Charge	$v_{\rm R} = 400 v$ $di_{\rm S}/dt = 200 \text{A}/\mu \text{s}$	$T_j = 125^{\circ}C$		5.4		μC



Temperature sensor NTC

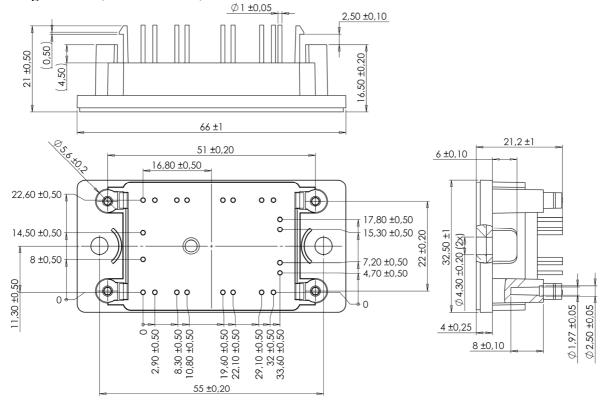
Symbol	Characteristic	Min	Тур	Max	Unit
R ₂₅	Resistance @ 25°C		22		kΩ
$\Delta R_{25}/R_{25}$	Resistance tolerance			5	%
$\Delta B/B$	Beta tolerance			3	/0
B 25/100	$T_{25} = 298.16 \text{ K}$		3980		K
	D				

 $R_{T} = \frac{R_{25}}{\exp\left[B_{25/100}\left(\frac{1}{T_{25}} - \frac{1}{T}\right)\right]}$ T: Thermistor temperature R_T: Thermistor value at T

Thermal and package characteristics

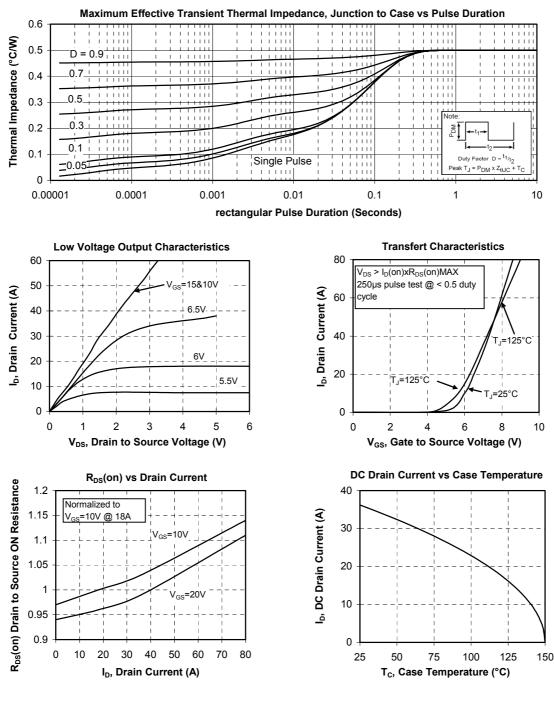
Symbol	Characteristic			Min	Тур	Max	Unit
V _{ISOL}	RMS Isolation Voltage, any terminal to case t =1 min, 50/60Hz			4000			V
T _J	Operating junction temperature range			-40		150	
T _{STG}	Storage Temperature Range			-40		125	°C
T _C	Operating Case Temperature			-40		100	
Torque	Mounting torque	To heatsink	M4	2		3	N.m
Wt	Package Weight					75	g

Package outline (dimensions in mm)



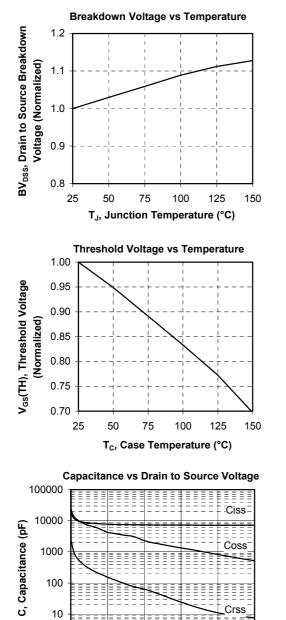


Typical Performance Curve (per CoolMOSTM)



APTC60HM83FT3G-Rev 1 October, 2012





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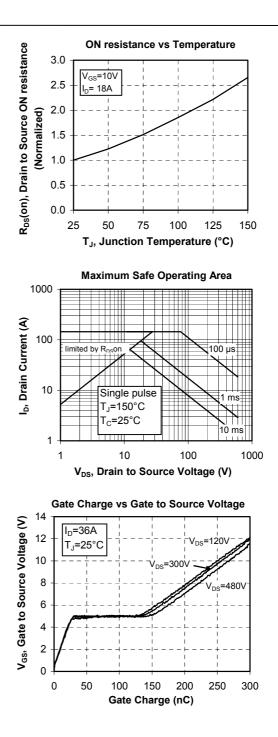
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V_{DS}, Drain to Source Voltage (V)

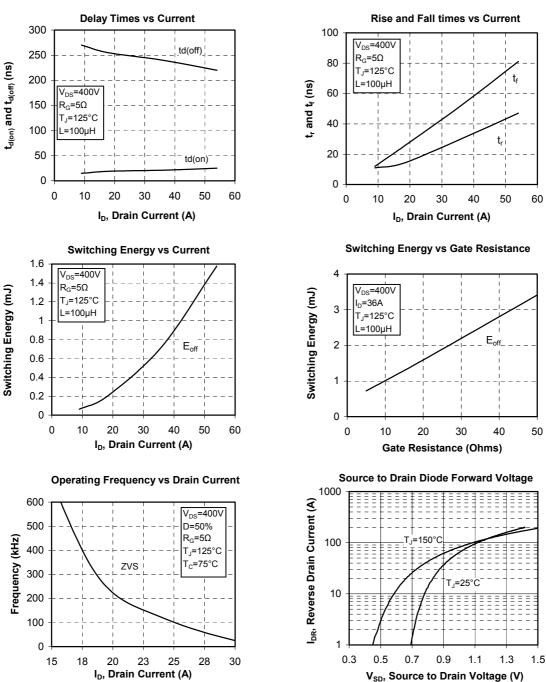
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APTC60HM83FT2G







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